Elektronische Bauelemente

2SD1767

0.7A , 80V

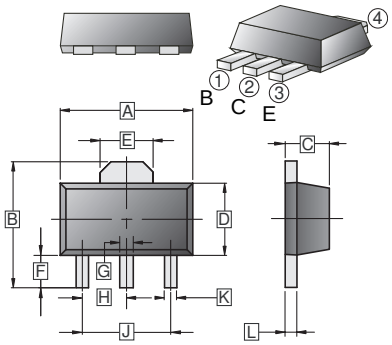
NPN Plastic Encapsulated Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- High Breakdown Voltage and Current
- Excellent DC Current Gain Linearity
- Complementary to 2SB1189

SOT-89

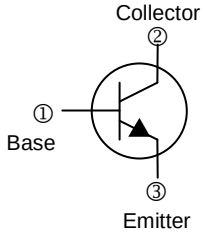


CLASSIFICATION OF h_{FE}

Product-Rank	2SD1767-P	2SD1767-Q	2SD1767-R
Range	82~180	120~270	180~390
Marking	DCP	DCQ	DCR

PACKAGE INFORMATION

Package	**MPQ**	**Leader Size**
SOT-89	1K	7 inch



REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	4.40	4.60	G	0.40	0.58
B	3.94	4.25	H	1.50 TYP	
C	1.40	1.60	J	3.00 TYP	
D	2.25	2.60	K	0.32	0.52
E	1.50	1.85	L	0.35	0.44
F	0.89	1.20			

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	**Symbol**	**Ratings**	**Unit**
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current-Continuous	I_C	700	mA
Collector Power Dissipation	P_C	500	mW
Maximum Junction to Ambient	$R_{\theta JA}$	250	℃ / W
Junction & Storage Temperature	T_J, T_{STG}	150, -55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	**Symbol**	**Min.**	**Typ.**	**Max.**	**Unit**	**Test conditions**
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80	-	-	V	I_C=50μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	-	-	V	I_C=2mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	-	-	V	I_E=50μA, I_C=0
Collector Cut-Off Current	I_{CBO}	-	-	0.5	μA	V_{CB}=50V, I_E=0
Emitter Cut-Off Current	I_{EBO}	-	-	0.5	μA	V_{EB}=4V, I_C=0
DC Current Gain	h_{FE}	82	-	390		V_{CE}=3V, I_C= 100mA
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	-	-	0.4	V	I_C=500mA, I_B= 50mA
Transition Frequency	f_T	-	120	-	MHz	V_{CE}=10V,I_C=50mA,f=100MH
Collector Output Capacitance	C_{OB}	-	10	-	pF	V_{CB}=10V, I_E=0, f=1MHz